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(54) **Title:** SYMMETRIC SEMICONDUCTOR PROCESSING CHAMBER

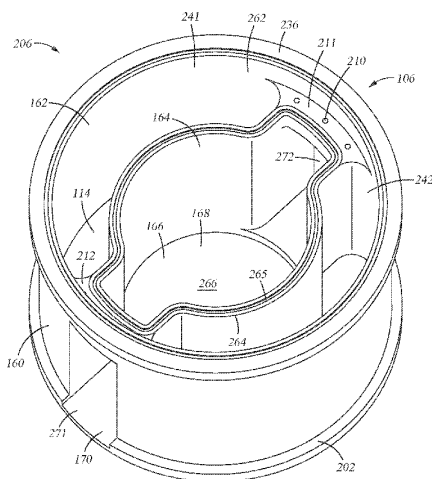


Fig. 2A

(57) **Abstract:** In one example, a flow module. The flow module has an inner wall and an outer wall equal-distant from the central axis. The flow module has radial walls connected between the outer wall and the inner wall, wherein the outer wall, inner wall and two or more pairs of radial walls define evacuation channels and a center portion. The center portion and evacuation channels are fluidly isolated from each other in the flow module. Two or more through holes are formed through the outer wall and fluidly coupled to the center portion. At least two of the two or more through holes are 180 degrees apart and linearly aligned through the central axis.

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